NSN 5961-01-041-0283

Inclosure Material:

Metal all transistor

Overall Length:

0.170 inches all transistor and 0.210 inches all transistor

Terminal Length:

1.500 inches all transistor

Overall Diameter:

0.209 inches all transistor and 0.230 inches all transistor

Internal Configuration:

Field effect all transistor

Channel Polarity And Control Type (non-core):

P-channel junction type all transistor

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-18 all transistor

Component Function Relationship:

Matched

Component Name And Quantity:

2 transistor

Mounting Method:

Terminal all transistor

Terminal Circle Diameter:

0.100 inches all transistor

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon all transistor

Voltage Rating In Volts Per Characteristic:

30.0 breakdown voltage, gate-to-source, with all other terminals short-circuited to source all transistor and 4.0 gate to source cutoff voltage all transistor

Current Rating Per Characteristic:

4.50 milliamperes zero-gate-voltage source current megawatts all transistor

Power Rating Per Characteristic:

300.0 milliwatts small-signal input power, common-collector absolute all transistor

Terminal Type And Quantity:

3 uninsulated wire lead all transistor

Shelf Life:

N/a

Unit Of Measure:

--

Demilitarization:

No

Fiig:

A110a0